

MOSFETs Silicon N-Channel MOS (DTMOSVI)

# TK190E60Z1

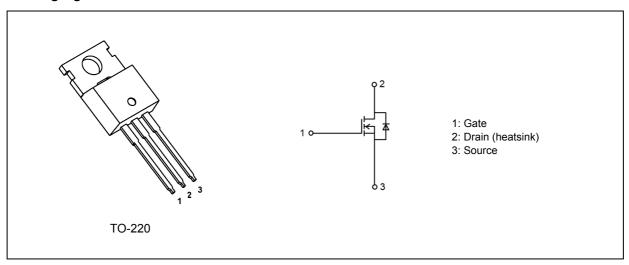
#### 1. Applications

· Switching Power Supplies

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.158 \Omega$  (typ.)
- (2) High-speed switching properties with lower capacitance.
- (3) Enhancement mode:  $V_{th} = 3 \text{ to } 4 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.48 \text{ mA})$

#### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	600	V
Gate-source voltage		V <sub>GSS</sub>	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	14	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	56	]
Power dissipation (T <sub>c</sub> = 25 °C)		P <sub>D</sub>	113	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	127	mJ
Single-pulse avalanche current		I <sub>AS</sub>	3.3	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	14	]
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	56	]
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	]
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

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Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2025-09



#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance		1.1	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	83.3	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25 °C (initial), L = 20.7 mH,  $I_{AS}$  = 3.3 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V			2	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600			٧
Gate threshold voltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 0.48 \text{ mA}$	3		4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS}$ = 10 V, $I_{D}$ = 4.2 A	_	0.158	0.190	Ω

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C <sub>iss</sub>	$V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}$	_	1060	_	pF
Reverse transfer capacitance		C <sub>rss</sub>		_	1.7	_	
Output capacitance		C <sub>oss</sub>		_	30	_	
Effective output capacitance (energy related)	(Note 3)	C <sub>o(er)</sub>	V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V	_	50		
Effective output capacitance (time related)	(Note 4)	C <sub>o(tr)</sub>		_	330		
Gate resistance		r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz	_	2.8	_	Ω
Switching time (rise time)		t <sub>r</sub>	See Figure 6.2.1	_	18	_	ns
Switching time (turn-on time)		t <sub>on</sub>		_	36	_	
Switching time (fall time)		t <sub>f</sub>		_	5	_	
Switching time (turn-off time)		t <sub>off</sub>		_	55	_	
MOSFET dv/dt ruggedness		dv/dt	$V_{DS} \le V_{DSS}, I_D \le 7 A$	70	_		V/ns

Note 3:  $C_{O(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{OSS}$  while  $V_{DS}$  is rising from 0V to 400V. Note 4:  $C_{O(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0V to 400V.

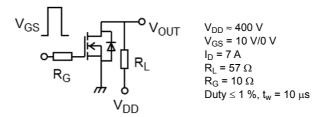


Fig. 6.2.1 Switching Time Test Circuit



## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 14 \text{ V}, I_D = 20 \text{ A}$	_	20	-	nC
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}$	_	6	_	
Gate-drain charge	Q <sub>gd</sub>		_	6	_	

## 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 14 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time		V <sub>DD</sub> = 400 V,	_	240	_	ns
Reverse recovery charge	Q <sub>rr</sub>	I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V -dI <sub>DR</sub> /dt = 100 A/μs		2.3	_	μС
Peak reverse recovery current	I <sub>rr</sub>	-αιρκ/αι – 100 Α/μδ	_	19	_	Α
Diode dv/dt ruggedness	dv/dt	$V_{DD} \le 400 \text{ V}, I_{DR} \le 7 \text{ A}, V_{GS} = 0 \text{ V}$	25	_	_	V/ns

## 7. Marking

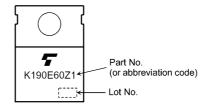


Fig. 7.1 Marking



### 8. Characteristics Curves (Note)

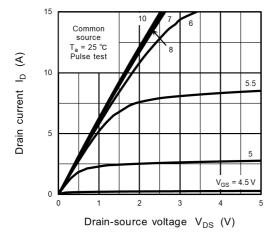


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

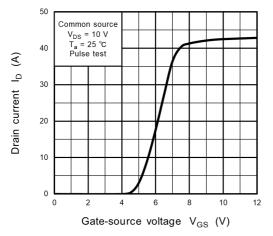


Fig. 8.3 ID - VGS

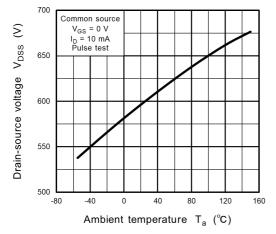


Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

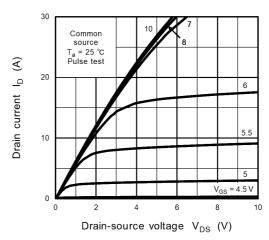


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

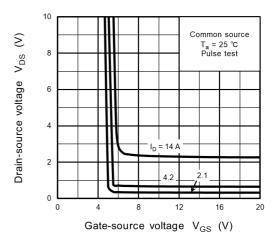


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

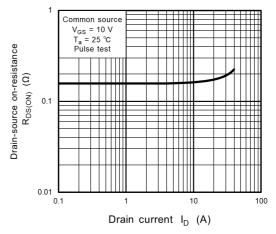
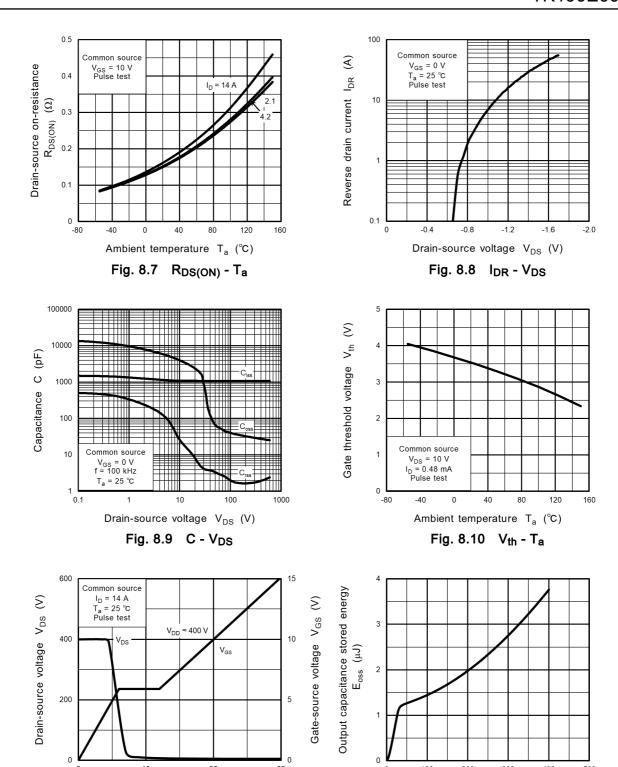


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>





Drain-source voltage  $V_{DS}$  (V) Fig. 8.12 Eoss -  $V_{DS}$ 



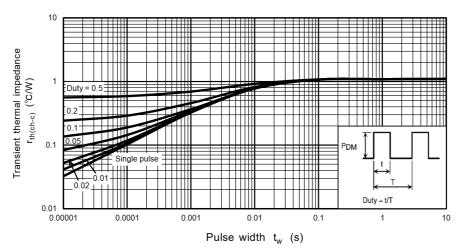


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

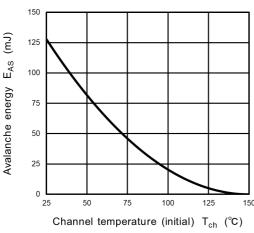
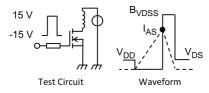


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)



$$V_{DD} = 90 \text{ V, L} = 20.7 \text{ mH} \quad E_{AS} = \frac{1}{2} \cdot \text{L} \cdot \text{I}_{AS}^2 \cdot \left( \frac{\text{B}_{VDSS}}{\text{B}_{VDSS} - \text{V}_{DD}} \right)$$

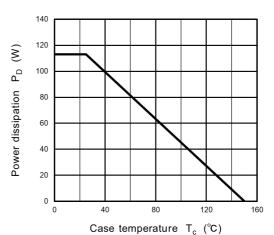


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

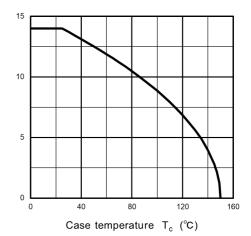


Fig. 8.17 I<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

Fig. 8.16 Test Circuit/Waveform

Drain current I<sub>D</sub> (A)



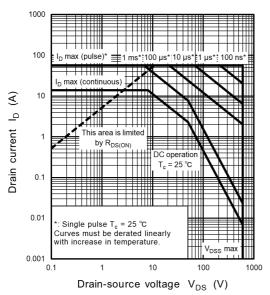


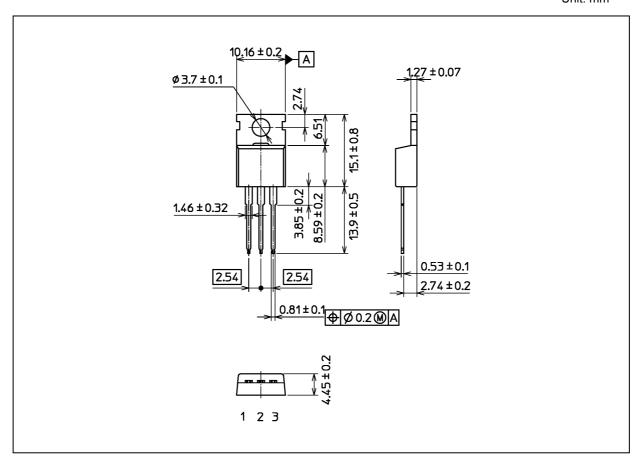
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 1.93 g (typ.)

Package Name(s)	
TOSHIBA: 2-10X1A	
Nickname: TO-220	



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